



R18000TM

The Latest SGI[™] Superscalar Microprocessor

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Silicon Graphics, Inc. www.sgi.com



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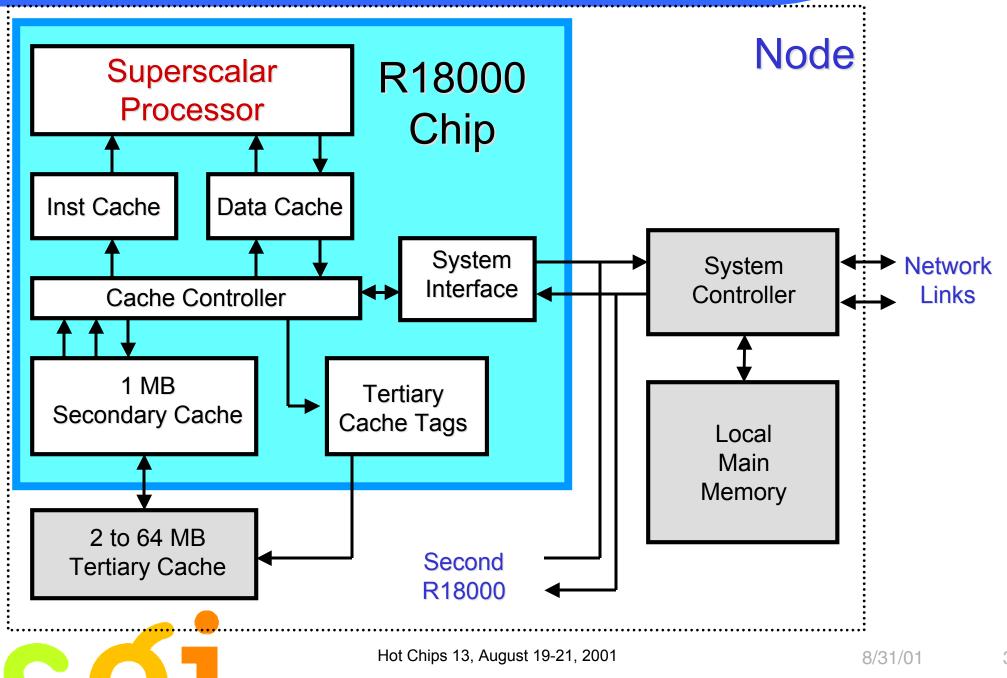




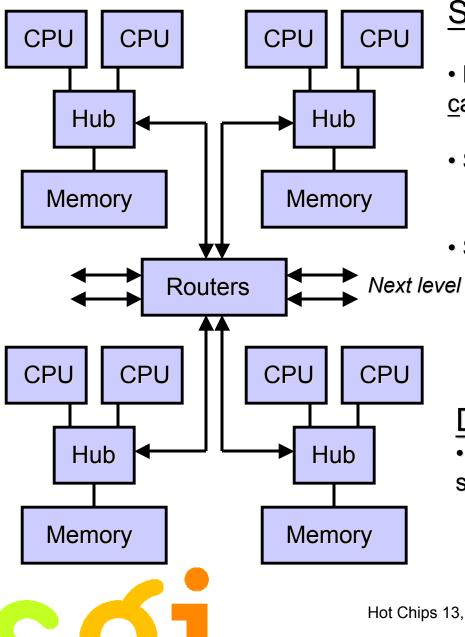
- R18000 Processor MicroArchitecture
- R18000 Memory Hierarchy
- Verification & Test
- Technology
- Summary



R18000 Chip Block Diagram



Scalable System Architecture



SGI's ccNUMA system architecture

- Local memories are shared in a <u>cache-coherent Non-Uniform Memory Architecture</u>.
- Single-system image (SSI).
 - Single shared address space.
 - Single copy of operating system.
- Scales to very large processor counts.
 - High-bandwidth network.
 - Low-latency in hubs and routers.
 - A dozen 512-p systems have been installed.

Design Challenge

- Keep processors and/or network busy even when streaming data from remote nodes.
 - Remote latency can be hundreds of cycles.
 - Time exceeds a dozen block transfers.

R18000 Processor MicroArchitecture

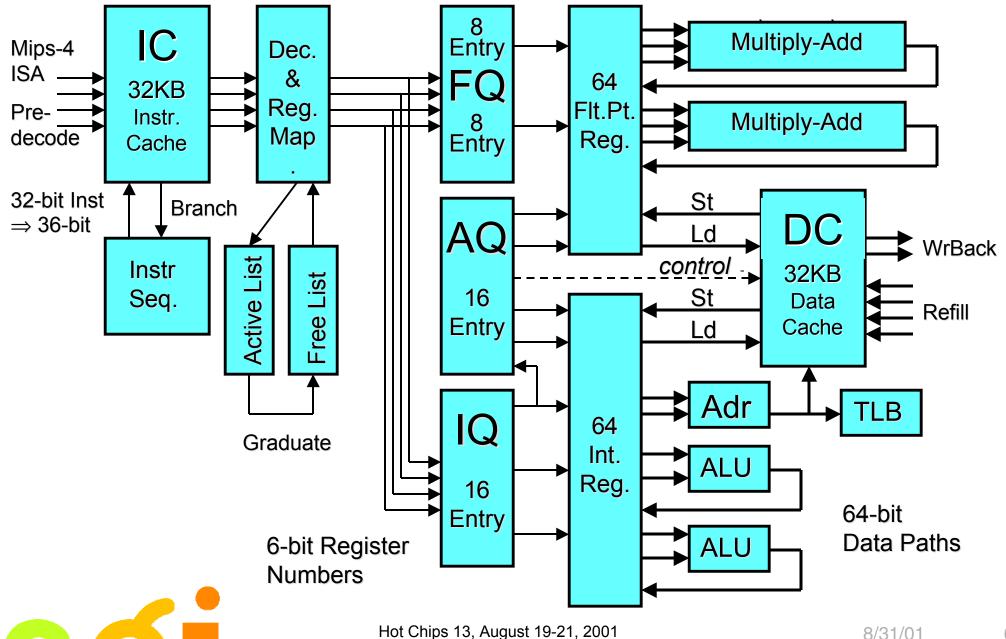
4-way super-scalar microprocessor

- Mips-4 Instruction Set Architecture
- Out of Order execution
- Two Floating-point Execution Units
 - Each issues one Add, Multiply or Multiply-Add instruction per cycle
- Large virtual and physical address spaces
 - 52-bit virtual address (data)
 - 48 bits physical address
 - Larger TLB page sizes 64M, 256M and 1G page sizes



R18000 Processor MicroArchitecture Processor Core Block Diagram



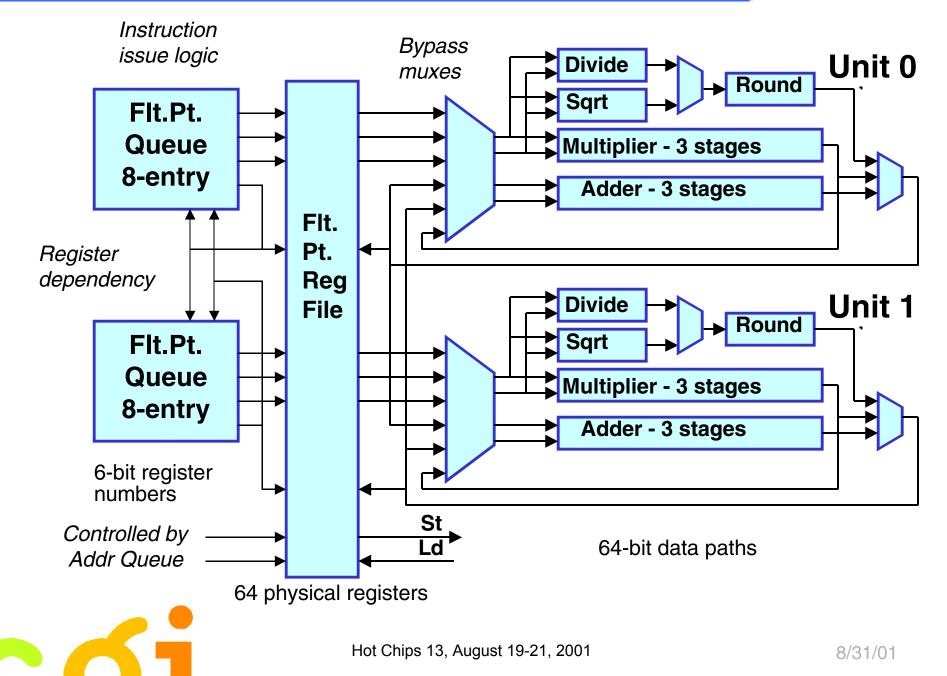




- Two floating-point execution units
 - Second unit doubles peak FLOPS rate
 - Each unit is controlled by an 8-entry Flt.Pt. queue
 - Each queue can issue one instruction per cycle:
 - Add
 - Multiply
 - Multiply-add
 - Multiplier and adder are pipelined
 - 1-cycle repeat rate
 - Latency increased to 3 cycles for faster clock rate
 - Divide and square-root units use iterative SRT algorithms



R18000 Processor MicroArchitecture Dual Floating Point Unit



• High bandwidth "SysTF" bus

- Uni-directional wiring with source-synchronous DDR clocking
- · 64-bit data path to hub chip, for addresses and write data
- 128-bit data path from hub chip, for read data and interventions
- Two processor chips share bus
- Programmable clock divisors
- Split transaction
 - Up to 28 outstanding operations (14 per processor).
- ECC protection
- SysAD mode for backward compatibility





- 3-level Cache hierarchy
 - L1: On-chip 32KB Instruction and 32KB Data cache
 - 2-way set associative
 - L2: On-chip 1M 4-way set associative on chip secondary cache
 - L3: Off-chip tertiary cache, up to 64 MB
 - On-chip tag
 - External cache is optional. Chip can operate with only internal caches

Subset property

- L1 and L2 lines must be subsets of L3
- Altered L1 lines must also be subsets of L2, to simplify write-back
- Refill from memory is loaded into on-chip L2, not into L3
- ECC protection on L2 and L3 caches, data and tags. (Parity on L1)
- Non-blocking operation. Write-back. LRU replacement algorithm
- Cache locking supported for L2 and L3



- On-chip secondary cache
 - 1 MB, 4-way set-associative, 128B line size
 - Two banks of multiple small arrays
 - Each bank has a write-back buffer for 8 cache lines
 - Copy entire line in one cycle
 - Operates at processor pipeline clock rate
 - Latency is less than half external cache latency. (5 to 6 cycles versus 12 to 14)
 - Bandwidth is 6 times greater than external cache
 - Simultaneous read and write at full internal bus bandwidths
 - Internal DDR clocking reduces wiring and noise
 - Read 4 quadwords per cycle <u>and</u> write 2 quadwords per cycle
 - All transfers are 64B packets, sent in two cycles
 - Reduces interference between instruction and data cache refills
 - Eliminates interference between refills and write-back





- Tertiary Cache Data Arrays
 - 4-way set-associative, 128B line size
 - Off-chip bandwidth is physically constrained by pin-out and wire length
 - 144 pins for 16 bytes data plus 8-bit ECC
 - Programmable clock rate. (Bit rate up to processor pipeline clock rate)
 - SDR or DDR synchronous SRAM, or
 - Fast DDR synchronous DRAM
 - Allows very large caches up to 64MB by 8-way sectoring
 - Same transfer rate as SRAM
 - Slightly longer latency is acceptable because:
 - Tertiary cache is only accessed if miss in secondary cache
 - Tertiary cache transfers 128-byte blocks
 - Latency is much less than main memory



Memory Hierarchy On-chip Tertiary Cache Tags



- Tertiary Cache Tags
 - 400-KB memory array contains:
 - 16,536 sets of four 52-bit address tags
 - ECC error check and correction on each cache set
 - Similar circuit design as on-chip secondary cache
 - Tag check is completed before accessing external data RAM
 - 4-way set-associative organization
 - L3 miss does not use any external RAM bandwidth
 - •Tag check and update take no external RAM bandwidth
 - System intervention to "snoop" cache cause minimal interference
 - Minimize latency for refill from main memory

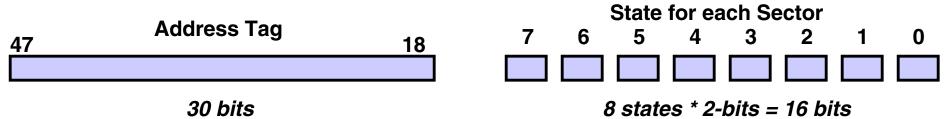


Memory Hierarchy Sectoring



• Size of on-chip cache tag array limits maximum size of off-chip cache. Sectoring raises limit from 8 MB to 64 MB.

• A single address tag can be used for 1, 2, 4, or 8 adjacent cache blocks ("sectors")



- Each additional sector requires only an extra 2-bit state
- Allows 8 times larger cache with only 50% larger memory array
 - An 8-sector tag represents a 1024-byte "macro-line"
 - Sectors are filled only when referenced
 - Victim tag may require up to 8 lines to be written back to main memory
 - "Lazy" write-back logic allows sectors to be refilled first
 - Only one X-queue entry is kept busy



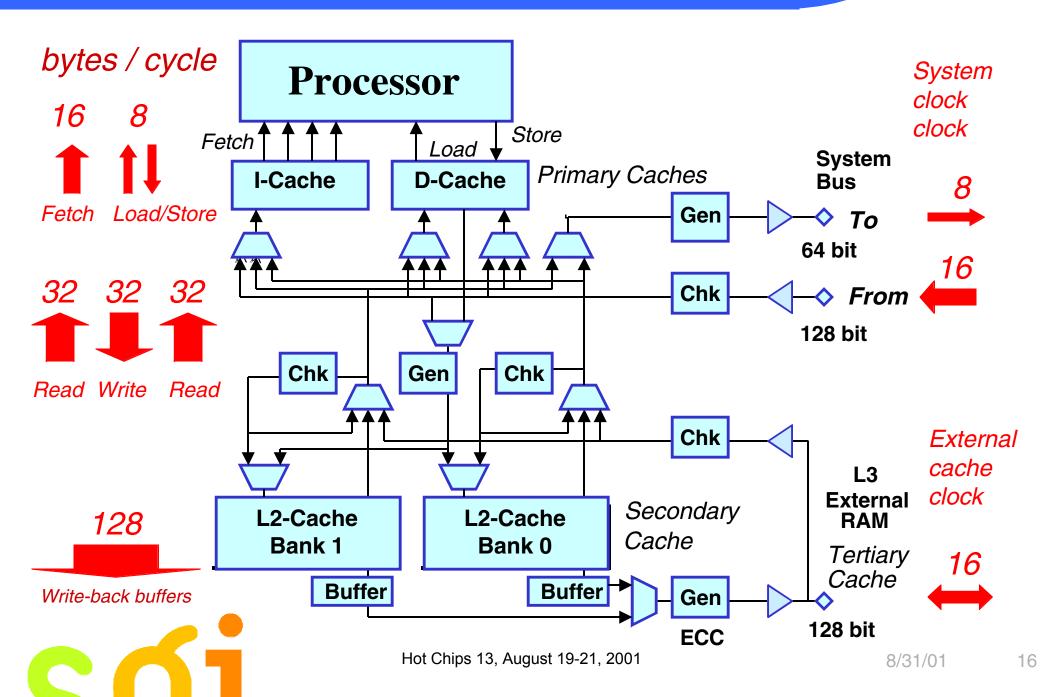


- Use parallel operation to achieve high performance
- Use high internal bandwidths to simplify logic design
- On-chip L2 cache is interleaved in 2 parallel banks
 - Each bank has separate read bus to processor
 - Data cache write-back bus is shared
 - Each bank is controlled by a separate X-Queue
 - Operations to different cache sets are independent
 - Cache bandwidth higher than read plus write buses combined
 - No interference between reads and writes
 - Easier arbitration
- Bandwidth of each internal bus higher than system bus plus external cache combined
 - Secondary cache can be refilled directly, with only minimum buffering



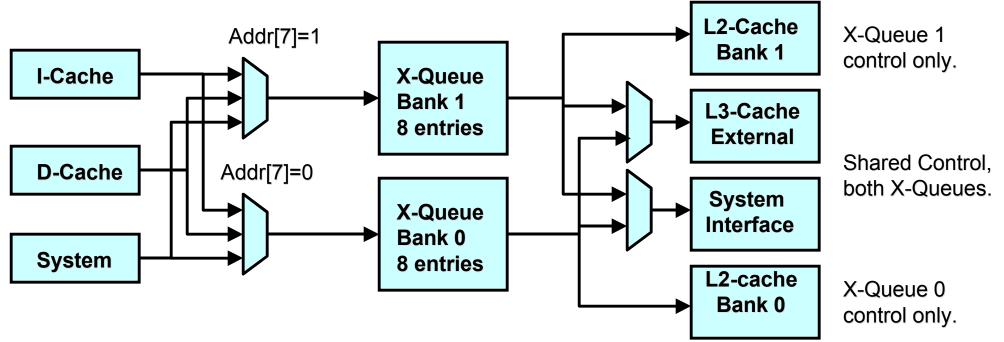
Memory Hierarchy High-Bandwidth Buses





Cache Control



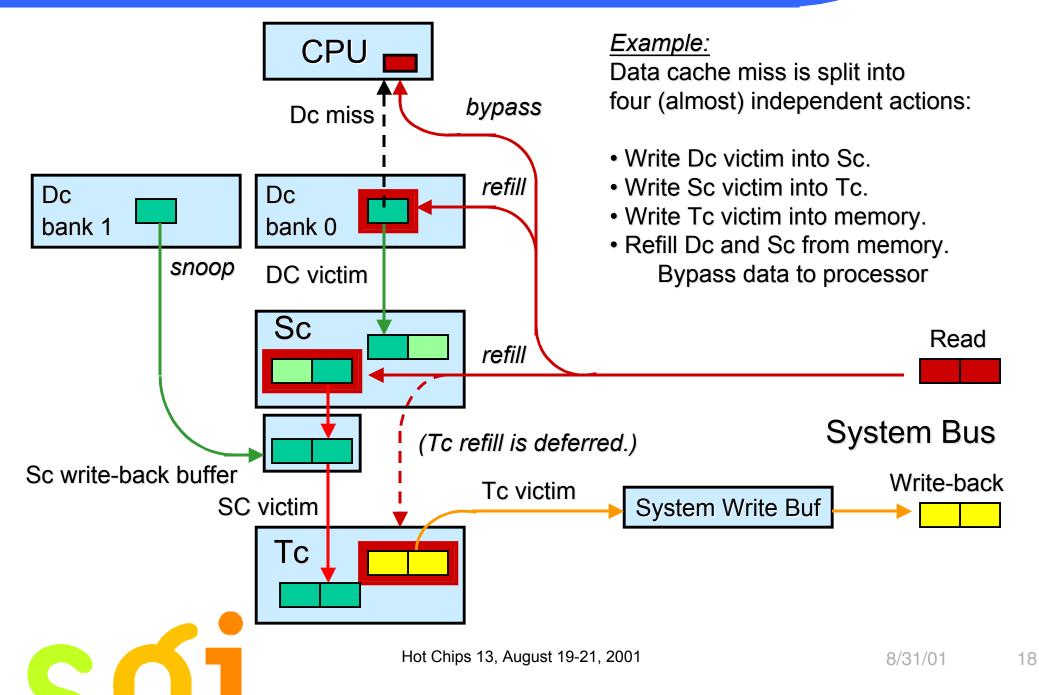


- 2 X-queues control external operations (L2 and L3 caches, system interface).
- Bank selected by Address[7], because L2 lines are 128 bytes.
- Each XQ contains 8 entries.
- Each entry contains 6 independent control fields for:
 - Primary caches.
 - Secondary cache read.
 - Tertiary cache read and write.
 - System bus read and write.



Cache Control Split operations into simple actions





Verification & Test

•Tools and environment:

- In house HDL and simulator with backup and replay..
- Graphical user interface for simulation and regression.
- Instruction level simulator as a reference machine.
- Programmable random code generators for UP and MP.
- C-based system model supports.
 - Cache arrays, memory controller and arrays, bus controller.
 - Bus protocol checking.
- 1 to 4 processor configuration for MP verification.

Diagnostics

- Architecture Verification Programs (AVP).
- Micro-architecture Verification Programs (MVP).
- Random diagnostics from programmable random code generators.
- Diagnostics are self-checked and/or compared with a reference machine.





Debugging Challenges

Activity hidden on chip (L1 and L2 caches).

Deep sub-micron features are difficult to observe in testers, impossible in a system.

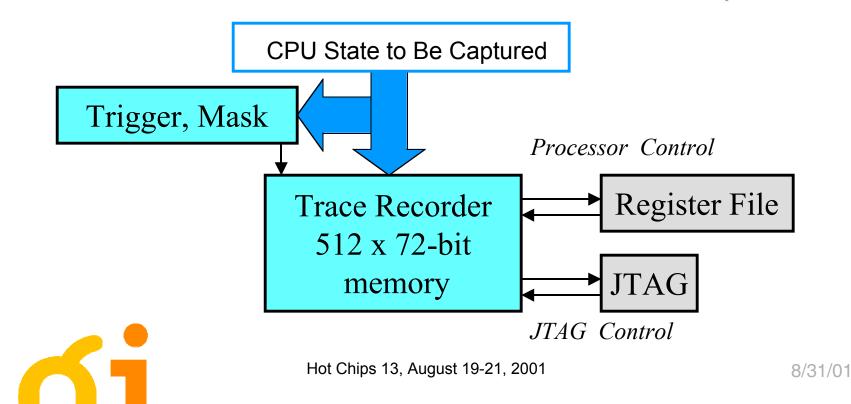
Large systems have many processors.

Failure point may be difficult to find.

Exact failure condition must be recreated.

On-chip Trace Recorder

512 x 72-bit trace memory (4 KB).
Records signals at processor clock rate.
Multiple trigger and recording options.
Configured by program or by JTAG.
Helps identify dynamic state of processor: cache refill, branch mispredict, ordering.





NEC's UX5 Advanced CMOS Technology

- Technology Generation
- Voltage
- Gate length
- Core oxide thickness
- Transistor current
- Leakage current
- 6T Memory Cell Area
- Interconnect wiring
- IMD Dielectric Constant

- : 130 nm
- : Vcc = 1.2 V
- : Lpoly = 95 nm
- : Tox < 19 Å
- : In >800, Ip >300 $\mu\text{A}/\mu\text{m}$
- : loffN or loffP <10 nA/ μ m worst case
- : < 3 μm²
- : 9 Layers Full Copper Damascene
- : < 3.0



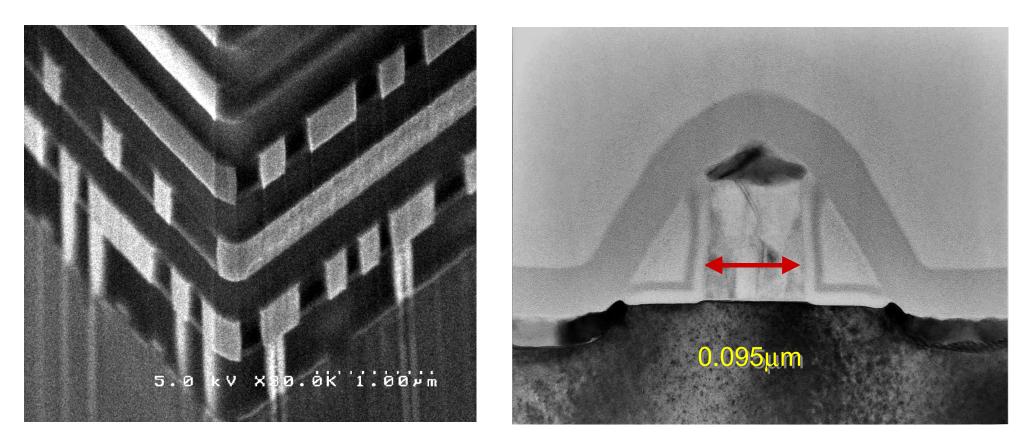
Technology



Scanning and Transmission Electron Microscope Images

•*Figure(a):* 3D SEM image of the metal stack on the core memory area

Figure (b): TEM image of R18000 device cross section. Achieving a 95nm gate length required a size reduction etch in combination with Krf lithography. A gate ReOx before extension formation reduces the Cov to less than 0.29 ff/ μ m.

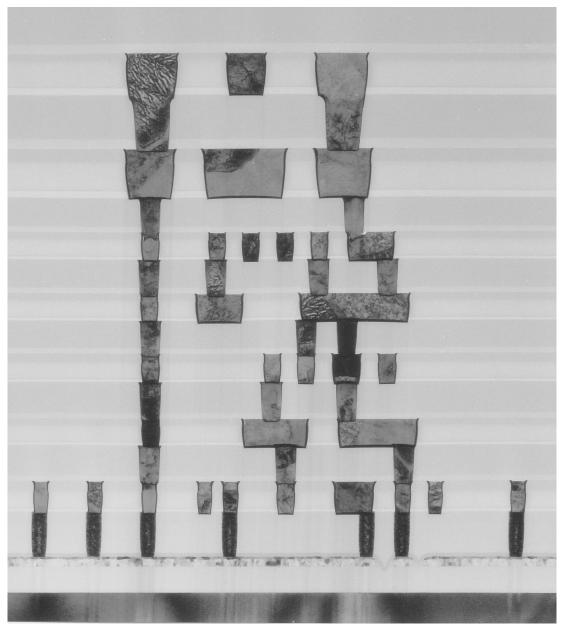




Technology



• *Figure (c):* TEM image of the metal stack for the R18000 core chip. Low K dielectric (Ladder Oxide) is used to reduce the lateral metal capacitance. Ladder Oxide offers comparable K value to SiLK with better thermal properties.







- R18000 is a high-performance superscalar microprocessor
 - Designed for use in large scalable ccNUMA systems
- Supported by a high-bandwidth system bus and a 3-level cache hierarchy
 - 1 MB on-chip secondary cache
 - On-chip tags support a 64 MB external cache, with sectoring
- Multiple banks and non-blocking operation improve cache performance
 - Each operation is split into multiple independent actions
- ECC protection
- Trace recorder supports system debugging

